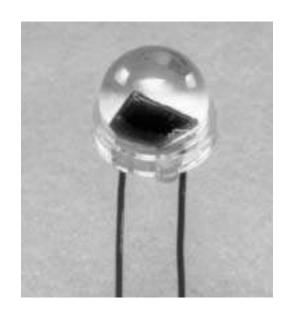
VTP Process Photodiodes

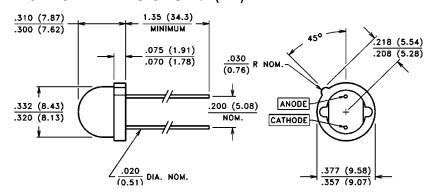
VTP1188SH



PRODUCT DESCRIPTION

Large area planar silicon photodiode mounted on a two lead ceramic substrate. A clear molded lens is used to increase sensitivity. Low junction capacitance permits fast response time.

PACKAGE DIMENSIONS inch (mm)



CASE 12 LENSED CERAMIC CHIP ACTIVE AREA: .017 in² (11 mm²)

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C

Operating Temperature: -20°C to 75°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | VTP11188SH | | | UNITS |
|--------------------|---|---------------------------------|------------|------|------|---------|
| | | | Min. | Тур. | Max. | - UNITS |
| I _{SC} | Short Circuit Current | H = 100 fc, 2850 K | | 200 | | μΑ |
| TC I _{SC} | I _{SC} Temperature Coefficient | 2850 K | | .20 | | %/°C |
| I _{SC} | Short Circuit Current | 100 μW/cm ² , 880 nm | 13 | | 25 | μA |
| V _{OC} | Open Circuit Voltage | H = 100 fc, 2850 K | | .33 | | mV |
| TC V _{OC} | V _{OC} Temperature Coefficient | 2850 K | | -2.0 | | mV/°C |
| I _D | Dark Current | H = 0, VR = 10 mV | | 3 | 30 | nA |
| R _{SH} | Shunt Resistance | H = 0, V = 10 mV | | 67 | | GΩ |
| TC R _{SH} | R _{SH} Temperature Coefficient | H = 0, V = 10 mV | | -11 | | %/°C |
| CJ | Junction Capacitance | H = 0, V =0 V | | .18 | .30 | nF |
| λ_{range} | Spectral Application Range | | 400 | | 1100 | nm |
| λ_{p} | Spectral Response - Peak | | | 925 | | nm |
| S _R | Sensitivity | @ Peak | | .55 | | A/W |